PTS3210

30V/10A N-Channel Enhancement Mode MOSFET

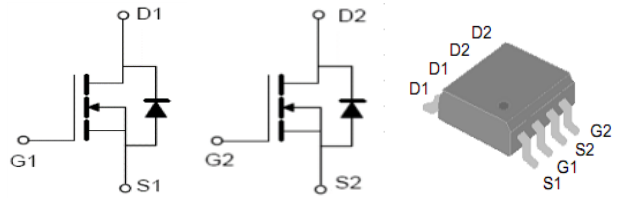
Features

- Improved dv/dt Capability, High Ruggedness·
- Maximum Junction Temperature Range (150°C)

BVDSS	30	V
ID	10	A
RDSON@VGS=10V	7.7	mΩ
RDSON@VGS=4.5V	11	mΩ

Applications

- High Side Load Switch
- Battery Switch
- Optimized for Power Management Applications for Portable Products, such as wireless charger, Media Tablets, PMP, DSC, GPS, and Others



SOP-8

Order Information

Product	Package	Marking	Reel Size	Reel	Carton
PTS3210	SOP-8	PTS3210	13inch	3000PCS	48000PCS

Absolute Maximum Ratings

Symbol	Parameter		Rating	Unit
Common Ratings (TC=25°C Unless Otherwise Noted)				
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage		30	V
V_{GS}	Gate-Source Voltage		±20	V
T_J	Maximum Junction Temperature		150	℃
T_{STG}	Storage Temperature Range		-55 to 150	℃
I_S	Diode Continuous Forward Current	TA =25°C	10	A
Mounted on Large Heat Sink				
I_{DM}	Pulse Drain Current Tested (Silicon Limit) (Note1)	TA =25°C	40	A
I_D	Continuous Drain current	TA =25°C	10	A
P_D	Maximum Power Dissipation	TA =25°C	2	W
$R_{\theta JA}$	Thermal Resistance Junction−to−Ambient (Note2)		62.5	°C/W

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Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ TJ = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain- Source Breakdown Voltage	VGS=0V ID=250μA	30	--	--	V
I_{DSS}	Zero Gate Voltage Drain current	VDS=30V,VGS=0V	--	--	1	μA
I_{GSS}	Gate-Body Leakage Current	VGS=±20V,VDS=0V	--	--	±100	μA
$V_{GS(TH)}$	Gate Threshold Voltage	VDS=VGS,ID=250μA	1	--	2.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance (Note3)	VGS=10V, ID=10A	--	7.7	13	mΩ
		VGS=4.5V, ID=10A	--	11	16	mΩ
Dynamic Electrical Characteristics @ T_J = 25°C (unless otherwise stated) (Note4)						
C_{iss}	Input Capacitance	VDS=15V, VGS=0V, F=1MHz	--	2097	--	pF
C_{oss}	Output Capacitance		--	170	--	pF
C_{rss}	Reverse Transfer Capacitance		--	126	--	pF
Q_g	Total Gate Charge	VDS=10V, ID=10A, VGS=10V	--	23	--	nC
Q_{gs}	Gate-Source Charge		--	7	--	nC
Q_{gd}	Gate-Drain Charge		--	5	--	nC
Switching Characteristics (Note5)						
$t_{d(on)}$	Turn-on Delay Time	VDS=10V, ID=10A, RG=2.7Ω, VGS=10V	--	14	--	nS
t_r	Turn-on Rise Time		--	9	--	nS
$t_{d(off)}$	Turn-off Delay Time		--	39	--	nS
t_f	Turn-off Fall Time		--	7	--	nS
Source- Drain Diode Characteristics@ TJ = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	IS=10A,VGS=0V	--	--	1.2	V

Note:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, t ≤ 10 sec.
3. Pulse Test: pulse width ≤ 300 us, duty cycle ≤ 2%.
4. Guranteed by design, not subject to production testing.

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Typical Characteristics

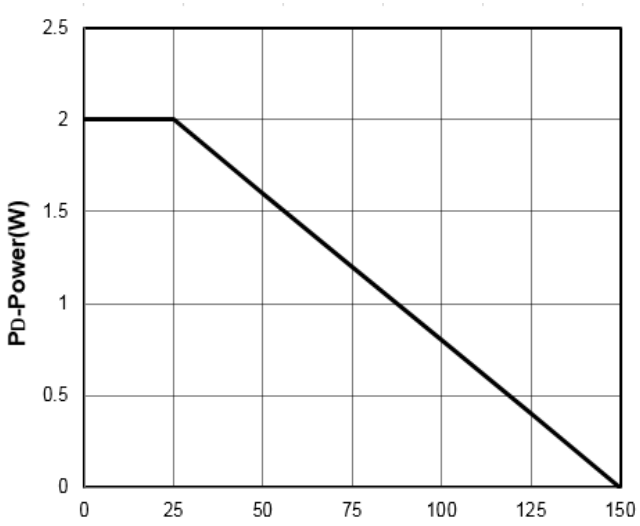

Figure1：T_J Junction Temperature（°C）

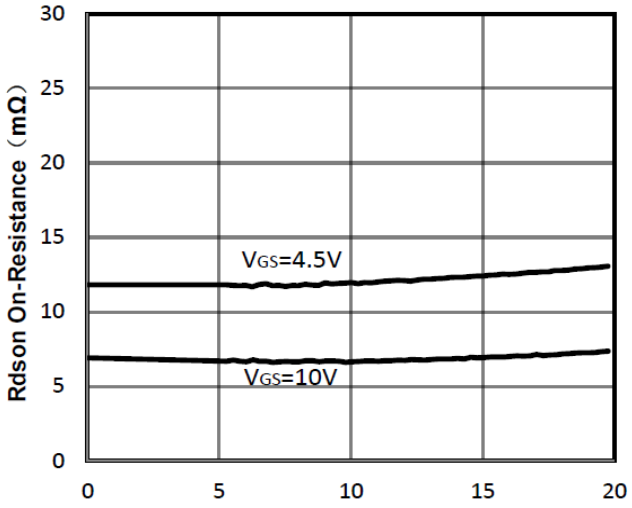

Figure2：I_D Drain Current（A）

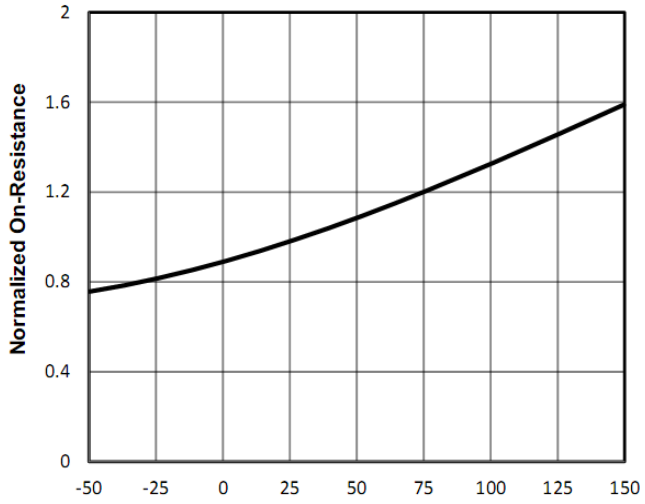

Figure3：T_J Junction Temperature（°C）

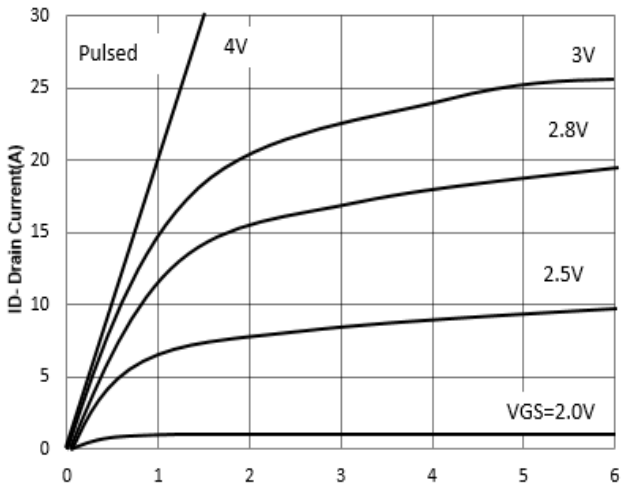

Figure4：V_{DS} Drain-Source Voltage（V）

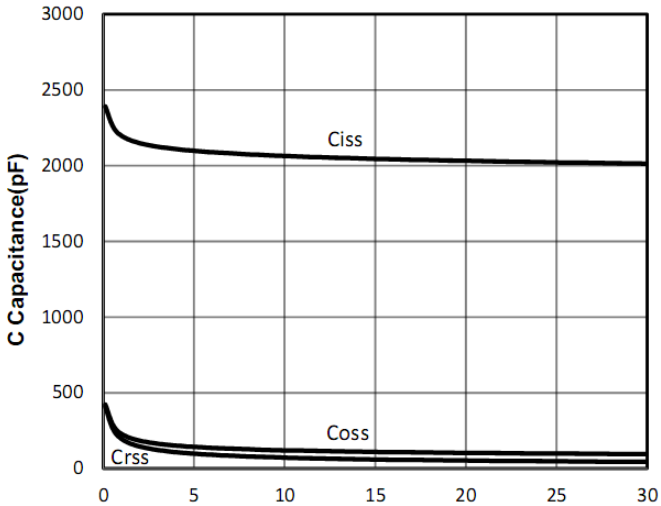

Figure5：V_{DS} Drain-Source Voltage（V）

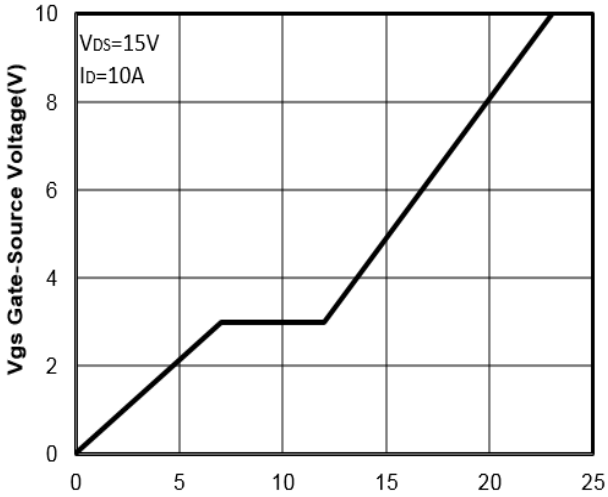

Figure6：Qg Gate Charge（nC）

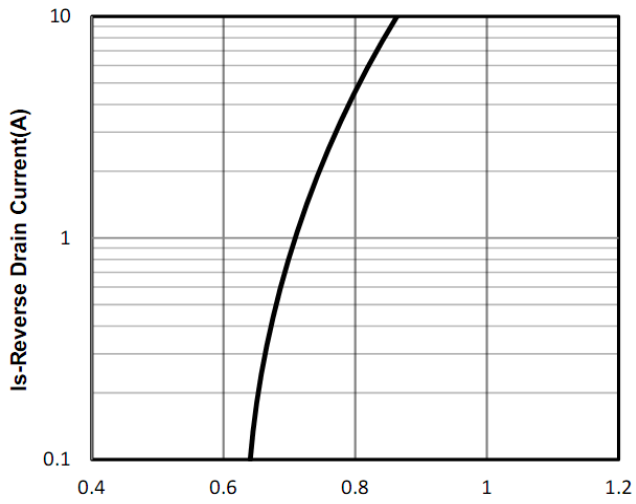

Figure7：Vsd Source-Drain Voltage（V）

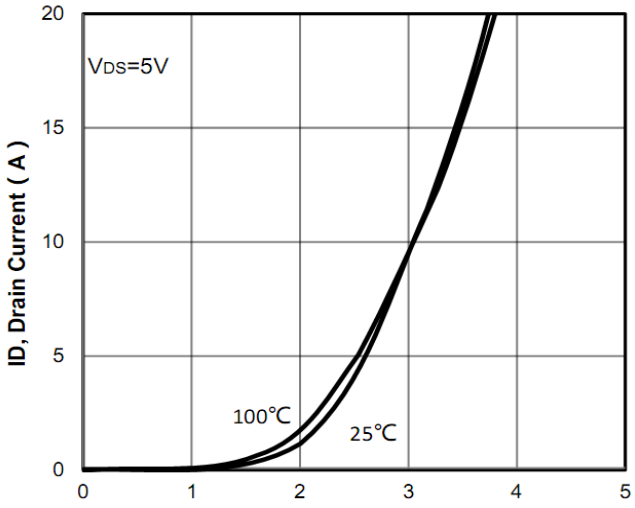

Figure8：Vgs Gate-Source Voltage（V）

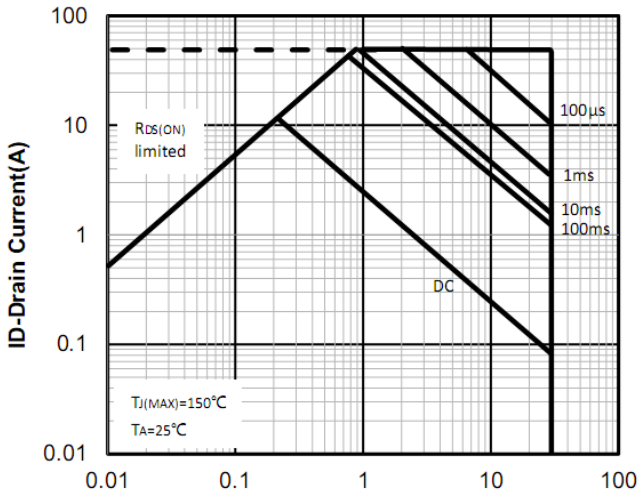

Figure9：Vds Drain -Source Voltage（V）

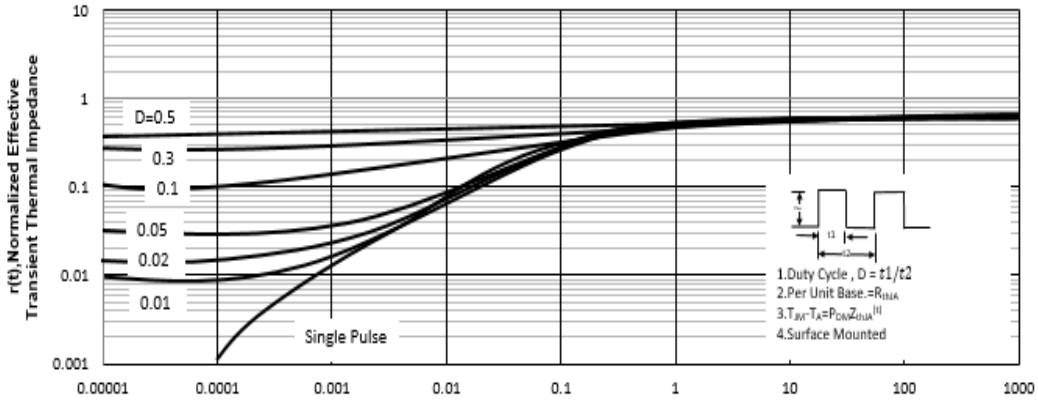

Figure10：Square Wave Pulse Duration（sec）

Test Circuit and Waveform:

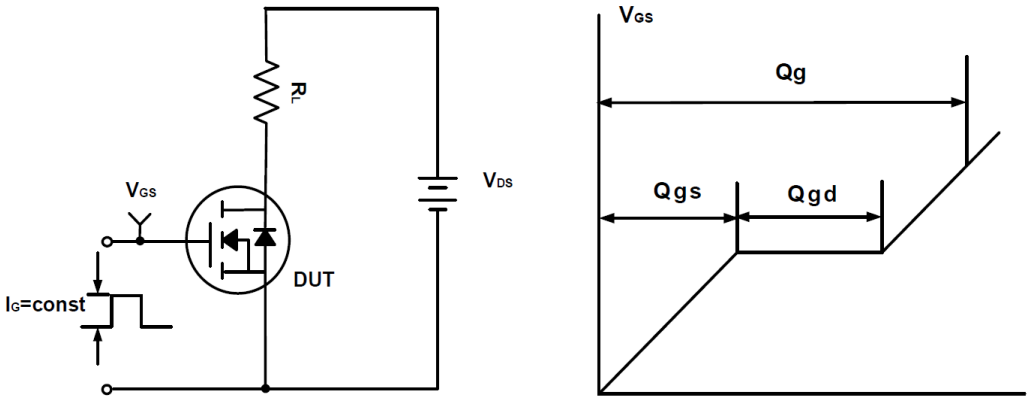

Figure A Gate Charge Test Circuit &Waveforms

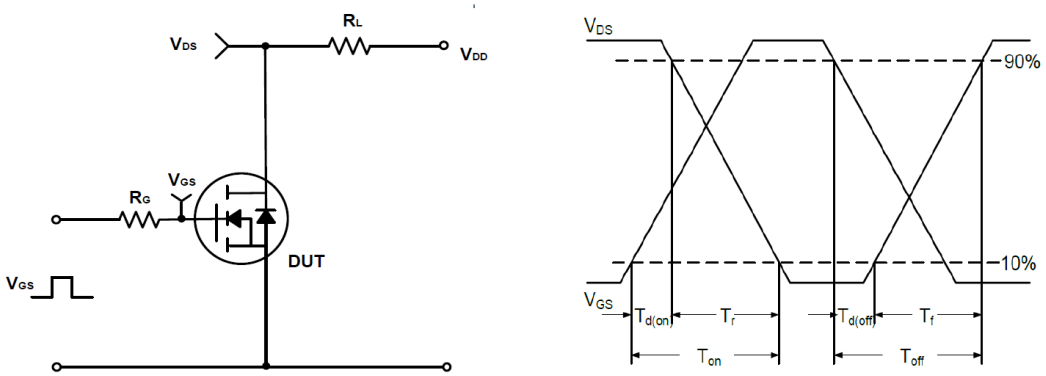

Figure B Switching Test Circuit & Waveforms

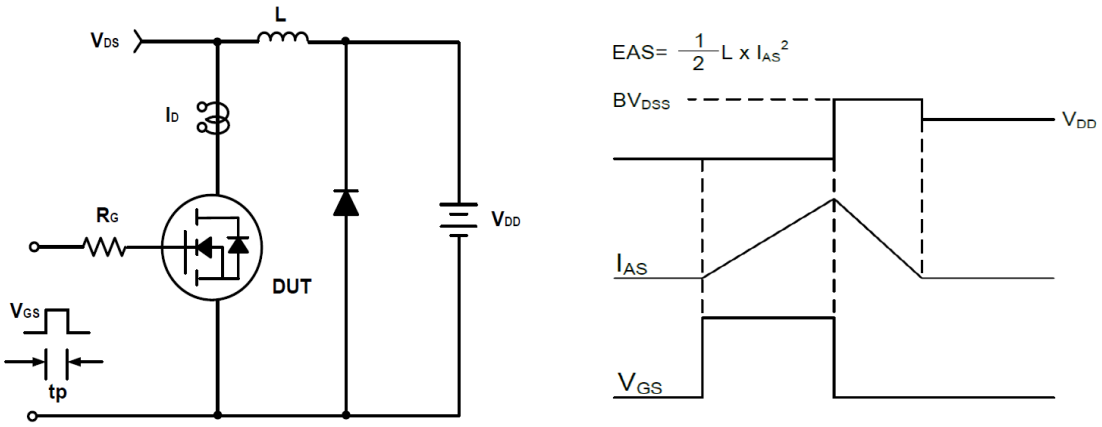

Figure C Unclamped Inductive Switching Circuit & Waveforms

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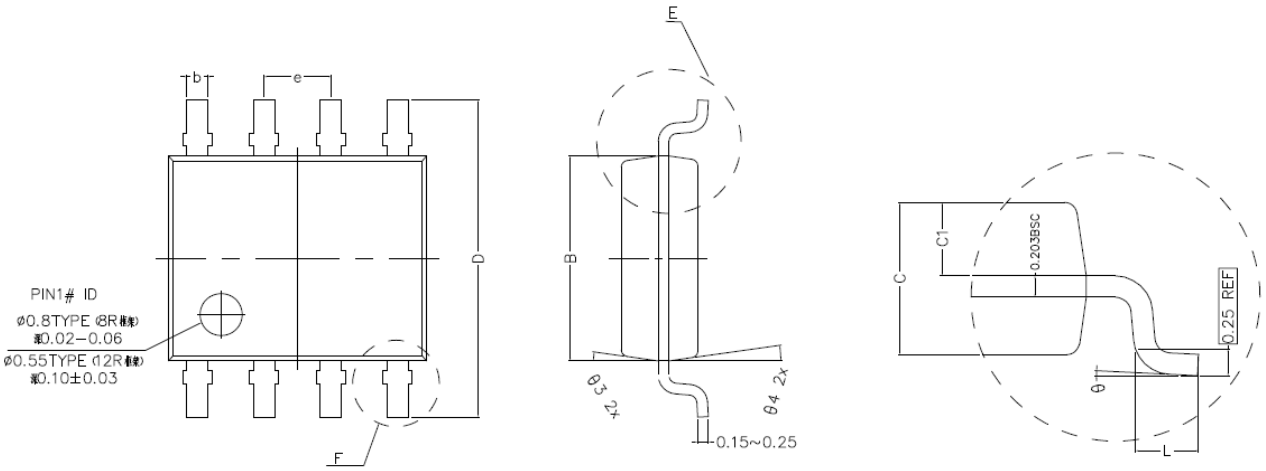
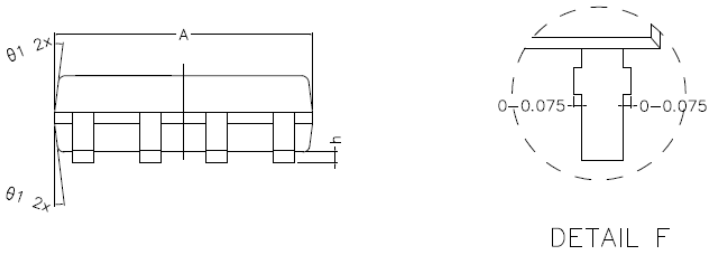
SOP-8 Package Outline Dimensions (Units: mm)





COMMON DIMENSIONS (UNITS OF MEASURE IS mm)			
	MIN	NORMAL	MAX
A	4.800	4.900	5.000
B	3.800	3.900	4.000
C	1.350	1.450	1.550
C1	0.650	0.700	0.750
D	5.900	6.100	6.300
L	0.500	0.600	0.700
b	0.350	0.400	0.450
h	0.050	0.150	0.250
e	1.270TYPE		
θ_1	7° TYPE(8R)	12° TYPE(12R)	
θ_2	7° TYPE(8R)	10° TYPE(12R)	
θ_3	8° TYPE(8R)	12° TYPE(12R)	
θ_4	8° TYPE(8R)	10° TYPE(12R)	
θ	0° ~ 8°		